

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(see as many sheets necessary)</i>				COMPLETE IF KNOWN	
				Application Number	Not Yet Assigned
				Filing Date	Not Yet Assigned
				First Named Inventor	Frestag
				Group Art Unit	Not Yet Assigned
				Examiner Name	Not Yet Assigned
SHEET	1	OF	1	Docket Number	HSJ9-2003-0070US1

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Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Office ³	Number ⁴			

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ⁵
AC		T. DIMOPOULOS et al., Enhanced robustness and tunnel magnetoresistance in artificial ferromagnet based tunnel junctions, Journal of Applied Physics, 1 May 2000, 4685-4687, 87-9	
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Examiner Signature	<i>MonCW</i>	Date Considered	4/12/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two letter-code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard St. 16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached.